

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	4	("6020614"   "6349067").PN. OR ("6633073").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/08 13:56
S1	213	(battery NEAR ("integrated circuit" OR semiconductor OR IC)) AND substrate AND (n-type OR diffusion) AND (electrode OR terminal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 18:28
S2	93	S1 AND ("solid state" OR solid-state)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 17:11
S3	4	("4965151" "5864182").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 17:12
S4	10	("4672586"   "5153710").PN. OR ("5864182").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/06 17:23
S5	18	("20010000744"   "4789648"   "4878094"   "5308720"   "5338625"   "5455126"   "5512147"   "5561004"   "5567210"   "5705293"   "5759911"   "5864182"   "5960254"   "5965459"   "5976928"   "6264709"   "6610440"   "6924164").PN. OR ("7045372").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/06 17:25
S6	16	("2800616"   "3536963"   "3558357"   "3634736"   "3648126"   "3656027"   "4014730"   "4737422"   "5437941"   "5455126"   "6123861").PN. OR ("6610440").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/06 17:26
S7	78	("4878094"   "5085953").PN. OR ("5338625").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/06 18:28
S8	6	S1 AND "diffusion layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 18:34

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S9	9	"battery mounted integrated circuit"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 18:38
S10	6	(battery NEAR ("integrated circuit" OR semiconductor)) AND (semiconductor NEAR substrate) AND ((first OR second) NEAR (diffusion OR "diffusion layer" OR n-type)) AND electrode AND concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 18:43
S11	39	(battery NEAR ("integrated circuit" OR semiconductor)) AND (semiconductor NEAR substrate) AND (first OR second) AND diffusion AND ("n-type" OR "n type")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 18:48
S12	5425	(Mino OR matsuda OR ito OR iwamoto AND Higuchi OR ugaji OR Shibano).in. AND battery	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 19:03
S13	7	S12 AND (battery NEAR substrate NEAR ("integrated circuit" OR substrate IC Or chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 19:31
S14	2	("5338625").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/06 19:32
S16	414	(257/798).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/07 11:14
S17	192	(257/924).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/07 11:14

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S18	1841	(257/724).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/07 11:41
S19	3012	(257/347).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/07 12:30
S21	2286	(battery OR "powersource") AND ((well OR region) NEAR (diffusion OR n-type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 12:32
S22	74	S21 AND battery.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 13:40
S23	63797	(257/666-796).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/07 13:40
S24	1061	S23 AND battery	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 16:30
S25	94	(solid-state NEAR thin-film NEAR battery) OR (Thin near Film near Solid near State near Battery)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 17:05
S27	112	(well NEAR isolation NEAR (n-type OR n-well OR "n well")) AND ("257" OR "438").clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 17:09

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S28	64	(well NEAR isolation NEAR (n-type OR n-well OR "n well")) AND n+ AND ("257" OR "438").clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 17:12
S31	3209	(ion NEAR (repel OR repluse OR repulsed OR repulsion OR repulsion OR repelled OR repulsive OR diffuse OR diffused OR diffusion OR diffusing)) AND ((region OR well OR area OR layer) NEAR (N OR N+ OR N-well OR P OR P+ OR P-well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 17:26
S32	3209	S31 AND ion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 17:27
S33	177	S31 AND battery	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 18:22
S34	24	((("solid state" OR solid-state) NEAR battery) AND (n-well OR n-type) AND diffusion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/07 18:37
S35	2	("4539660").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/07 18:37
S36	15	("4247913"   "4384350").PN. OR ("4539660").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/07 18:38